PROCESS FOR THE PRODUCTION OF SEMICONDUCTOR DEVICE

ABSTRACT OF THE DISCLOSURE:

A process for the production of a semiconductor device, comprising the steps of (A) forming a concave portion in an insulating interlayer formed on a substrate so that part of the substrate is exposed in a bottom of the concave portion, (B) forming a first electrically conductive layer on the insulating interlayer including an inside of the concave portion, by an electroless plating method, and (C) forming a second electrically conductive layer on the first electrically conductive layer by an electroplating method, to fill the concave portion with the second electrically conductive layer.

FIGURE 7B